

Cont'd

C1

an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film, wherein a thickness of the TaN film is 20 nm or more; and
an Al film formed on the Ta film and used as a pad.

- C2*
15. (Twice amended) The semiconductor device according to claim 1, wherein a thickness of the TaN film is 40 nm or more.
16. (Amended) A semiconductor device comprising:
a Cu film provided above a main surface of a semiconductor substrate and used as a wiring;
an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film;
an Al film formed on the Ta film and used as a pad, the Al film having an extending portion under which the Cu film is not formed; and
a conductive connection member connected to the Al film at the extending portion.

- C3*
21. (Twice amended) The semiconductor device according to claim 16, wherein a thickness of the TaN film is 20 nm or more.
22. (Twice amended) The semiconductor device according to claim 16, wherein a thickness of the TaN film is 40 nm or more.

REMARKS

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In the present Amendment, claim 14 has been canceled, without prejudice or disclaimer of the subject matter thereof. Applicants propose amending claims 1, 15, 16, 21 and 22 to more appropriately define aspects of their invention. Upon entry of the amendment, claims 1-13 and 15-22 will remain pending.